

IN THE CLAIMS:

Please cancel Claims 3 and 7 without prejudice to or disclaimer of the subject matter presented therein. Please amend Claims 1 and 6 as shown below.

1. (Currently Amended) A method of producing a photovoltaic device, comprising steps of:
- forming a zinc oxide layer on a substrate at least by electrolytic deposition;
- subjecting the zinc oxide layer to any one treatment selected from the group consisting of plasma treatment with a rare gas or nitrogen gas, ion irradiation, light irradiation and electromagnetic irradiation; and
- forming on the zinc oxide layer a semiconductor layer comprising a non-single crystal silicon material containing hydrogen and having at ~~least~~ least one p-i-n junction,
- wherein before forming the zinc oxide layer, another zinc oxide layer is formed on the substrate by sputtering and is used as an underlying layer,
- wherein an adsorption preventive layer is provided between the zinc oxide layer and a p- or n-type semiconductor layer provided adjacent to the zinc oxide layer, and
- wherein the adsorption preventive layer comprises a non-single crystal silicon material in which an amount of dopant is decreased compared to the p- or n-type semiconductor layer provided adjacent to the zinc oxide layer.

2. (Original) The method of producing a photovoltaic device according to claim 1, wherein the treatment is a rare gas plasma treatment using at least one rare gas selected from the group consisting of He, Ne, Ar, Kr and Xe.

3. (Cancelled)

4. (Original) The method of producing a photovoltaic device according to claim 1, wherein the average thickness of the zinc oxide layer is from 10 nm to 5 μ m inclusive.

5. (Original) The method of producing a photovoltaic device according to claim 1, wherein the zinc oxide layer transmits 50% or more of light with a wavelength of 800 nm.

6. (Currently Amended) The method of producing a photovoltaic device according to claim 1, wherein the zinc oxide layer has a resistivity lower than that of [[a]] the p- or n-type semiconductor layer provided adjacent to the zinc oxide layer.

7. (Cancelled)